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Brückewell

Company Presentation www.bruckewell-semi.com 2022

Company Description



Company Description

Discrete Wafer Design Own-Brand Device Exceptional Value

Bruckewell technology Co LTD is a discrete semiconductor design company that have the able to offer KGD wafer-level products to provide silicon and wide bandgap (WBG) power semiconductor devices We pride ourselves in our expertise in all areas of power semiconductor technology and business operations, our technical team that from Vishay & Infineon contributes over 25 years expertise in power semiconductor.



LOGO Significance



Bruckewell comes from the German "Brücke", meaning "bridge" and English "well" To become synonymous with technical innovation and timely marketing partner The green leaf symbol reflects taking an active part in health & safety and protecting the environment as our responsibility



Company History 公司沿革

Creation of the company Began its business on semiconductor material electronic components in San Jose, California.

Bruckewell technology corp. registered in Delaware, USA. Bruckewell最初註冊登記在美國德拉瓦州,從材料及元件銷售

Start Wafer Development Headquarter in Taiwan

- Bruckewell Technology Corp., Ltd. registered in Taiwan
 - 在台灣登記為雋佾科技以開始銷售自有品牌及設計晶圓

開始進入市場

Semiconductor division founded in Taiwan for discrete semiconductor wafer design and branded products.

First Schottky Diode Wafer came by 10A, 100V



2009



Company History 公司沿革

Offering the AEC-Q101 (車用認證) Grade wafer 首批車用認證二極管及場效電晶體產品通過客戶承認,

Follow the AEC –Q101 standard to design and control the product, customer approved for MOSFET/Diode Products.





Bruckewell has been separated from Elan Group 2021 Focus on the SiC series products



Strategy Partner with Taiwan GTM 2019 合併勤益電子事業部

2012

建立可靠度實驗室及封裝技術支持

Prater with Foxcoon, Vishay

與鴻海,威世通用簽訂戰略夥伴

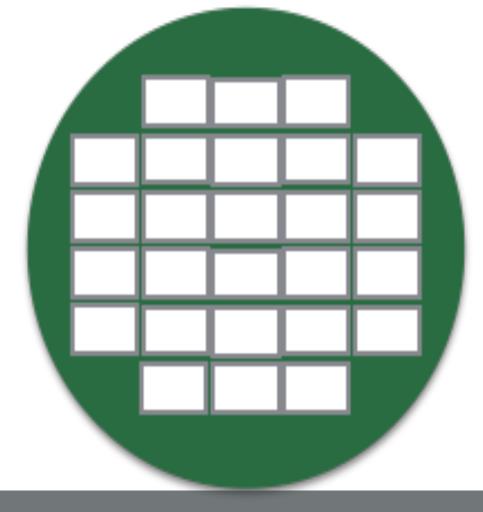


Products/Service





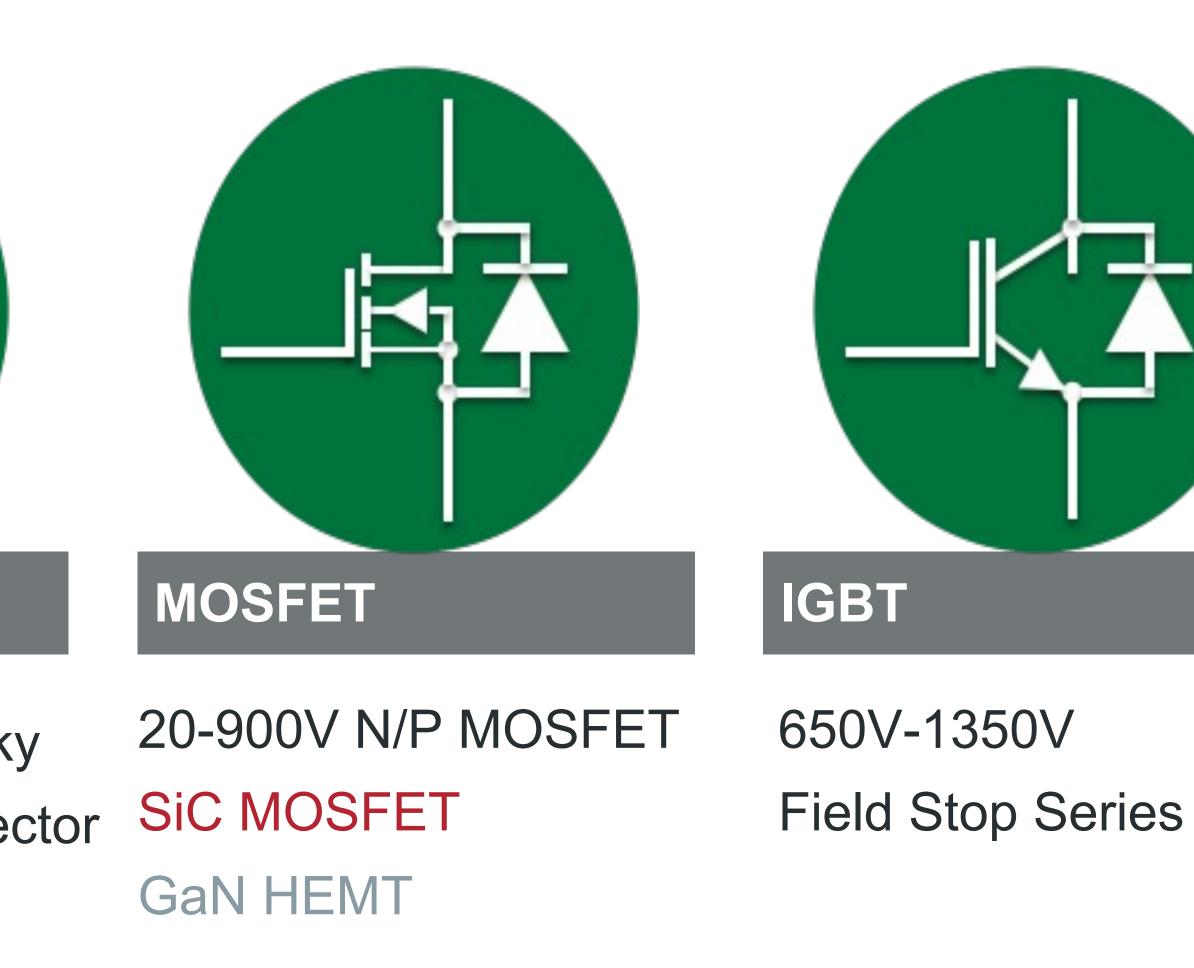
Our Products



Bare Wafer

Diode MOSFET TVS/Zener IGBT Standard/ Fast/ Schottky TVS/ Zener/ ESD Protector SiC Schottky Diode

Diode









Regional Distributors Presence

Advanced MP Technology Inc. **AVR Global Technologies**

USA



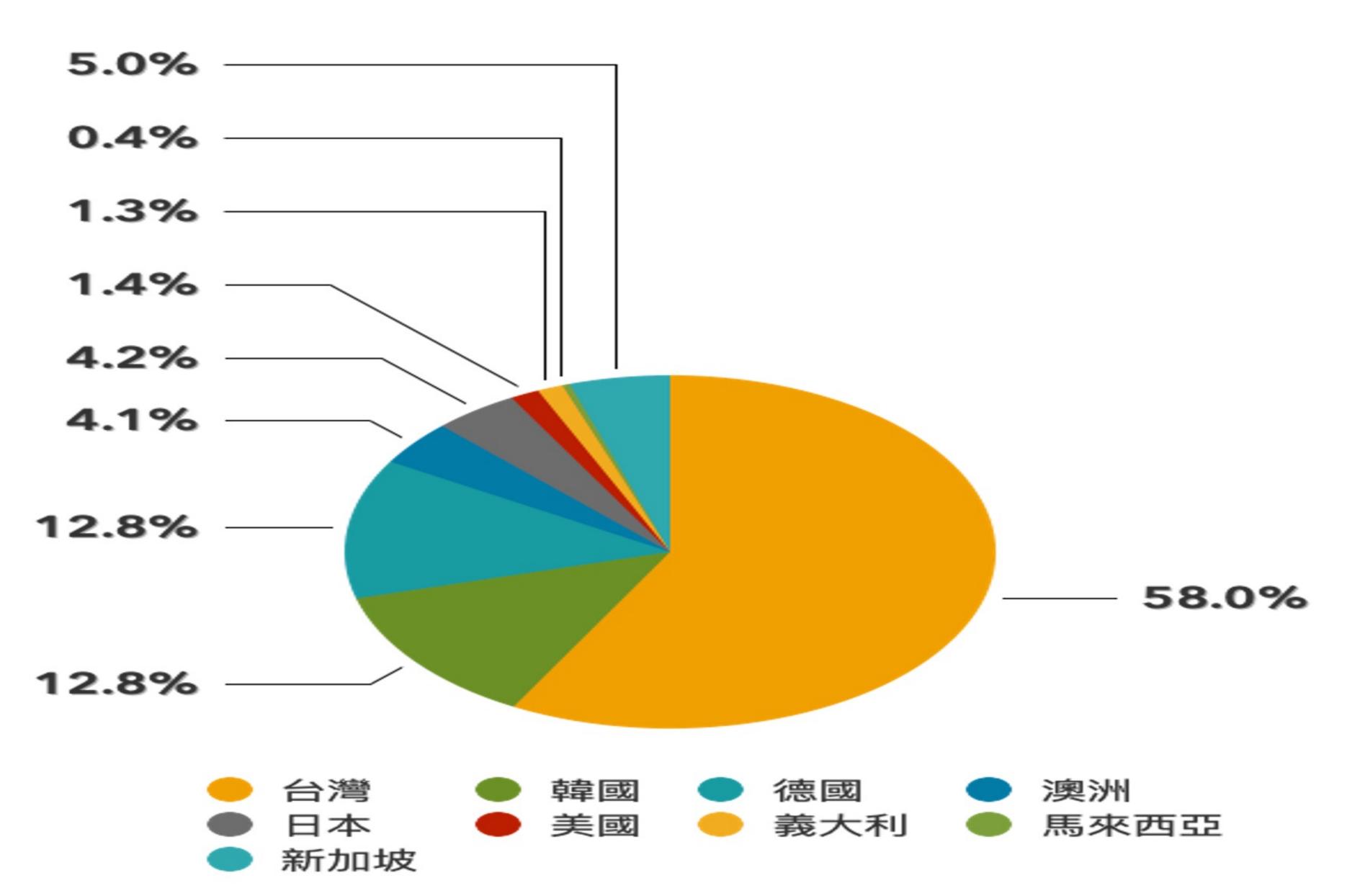
EIL Company Ltd, HK, Shanghai, Shenzhen Protech Century Limited. HK, Shenzhen Cheng Sheng Industrial Co., Ltd, Shanghai Smart Technology Co. Ltd, HK GH Development Holdings Limited. Shenzhen

CARIS, Vietnam





Marketing by Countries-2021



Quality/ Environmental Policy

Our goal is to exceed the quality expectations of our customers. It is achieved through innovation, technical excellence and continuous improvement 我們的目標是超越客戶的質量要求。通過創新,技術精益求精,持續改進

Bruckewell commit to work with our customers to offer products that address the environmental concerns of our industry. **RoHS/WEEE/ REACH Compliance**

Bruckewell offers lead-free products as defined in the European Union's RoHS Directive 2011/65/EU and are compatible with the current RoHS requirements for all six banned substances.

Bruckewell Devices offers products that support the EU decree 1907/2006.

Independent Analysis -Bruckewell provides independent laboratory SGS reports







Quality Compliance

RoHS Compliant







MATERIALDATA SYSTEM IMDS for Automotive

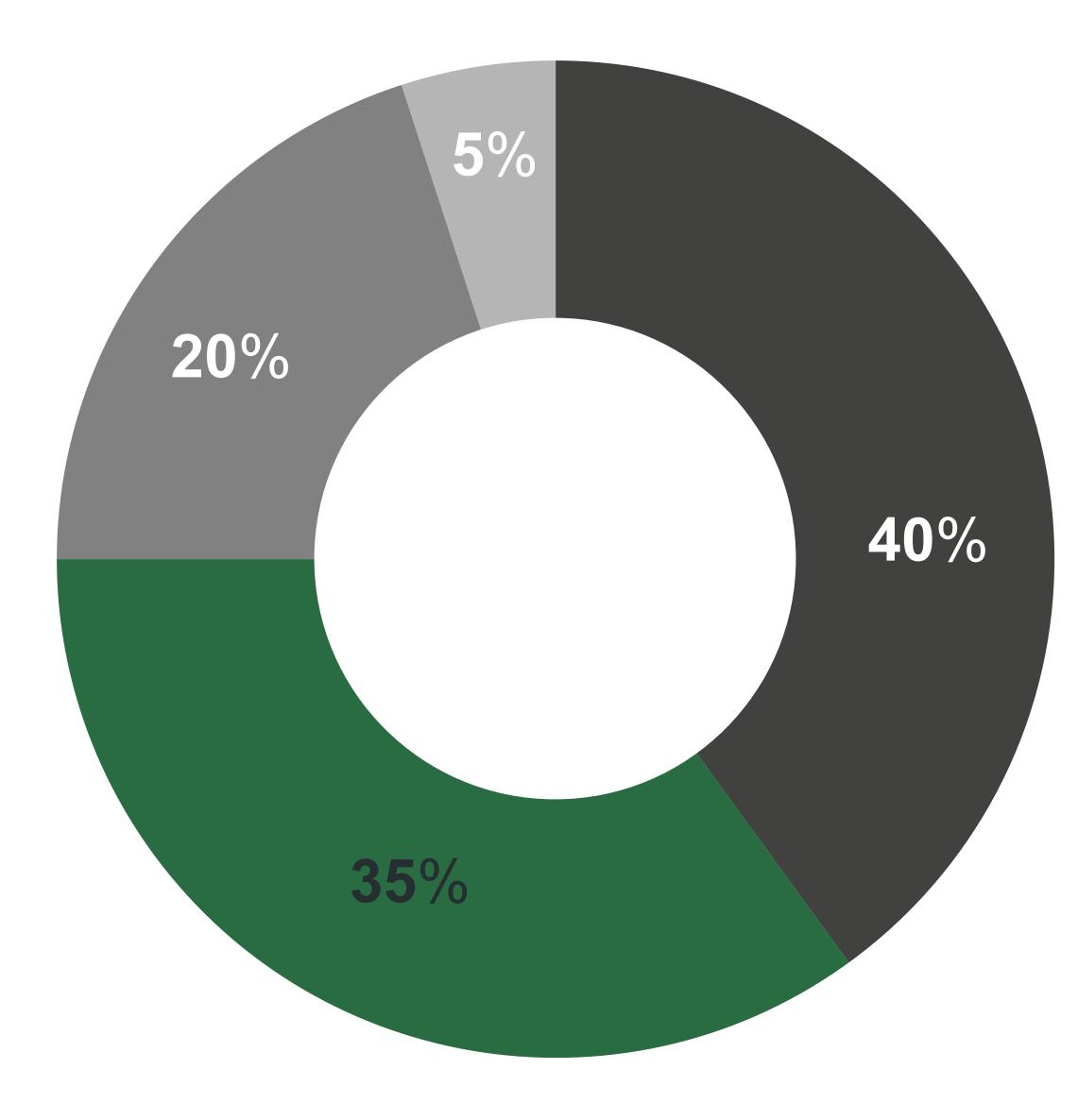


Patent Awards

- Silicon Carbide Surfaces Area and Optimization Improvement
- Silicon Silicide Area and Optimization
- Silicon Power Mosfet Low Voltage Structure, WAVYFET
- Lateral Passivated Schottky structure
- Silicon Silicide Area and Optimization—USA
- □ PBR Diode Wave Diode Structure—TAIWAN, USA
- □ SG MOSFET Process Method—TAIWAN, USA



Balanced Product Portfolio



2021

Ultra Low RDS(on) Shield Gate MOSFET Technology Platform development bring the 100V products to service EV application. 6th Field Stop IGBT products Ready 650V, 1200V SIC JBS Diode Ready

1	Diodes	2	Bare Die/ ODM
3	MOSFETs	4	SiC Diode GaN-FET IGBT



Sales and Marketing



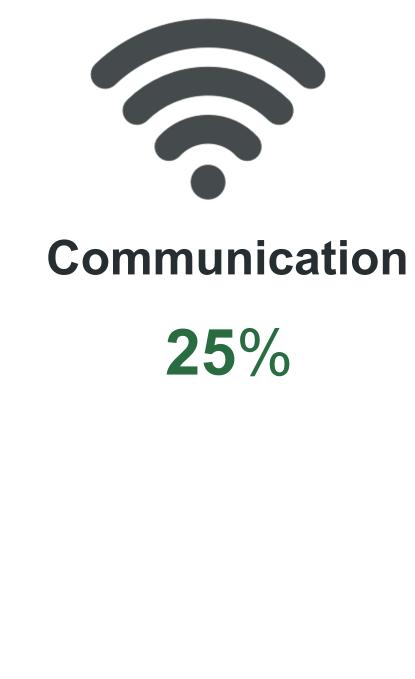
AC-DC/ DC-DC power supply Battery power supply Switched-mode power supply Home appliance/ multimedia LED Lighting



Automotive

20%

Automotive/ E-Bike Car Audio Car Headlight



PLC, Power Line Communication ProE, Power over Ethernet IP Cam, Internet protocol Cameras Telecommunication Cell Phone

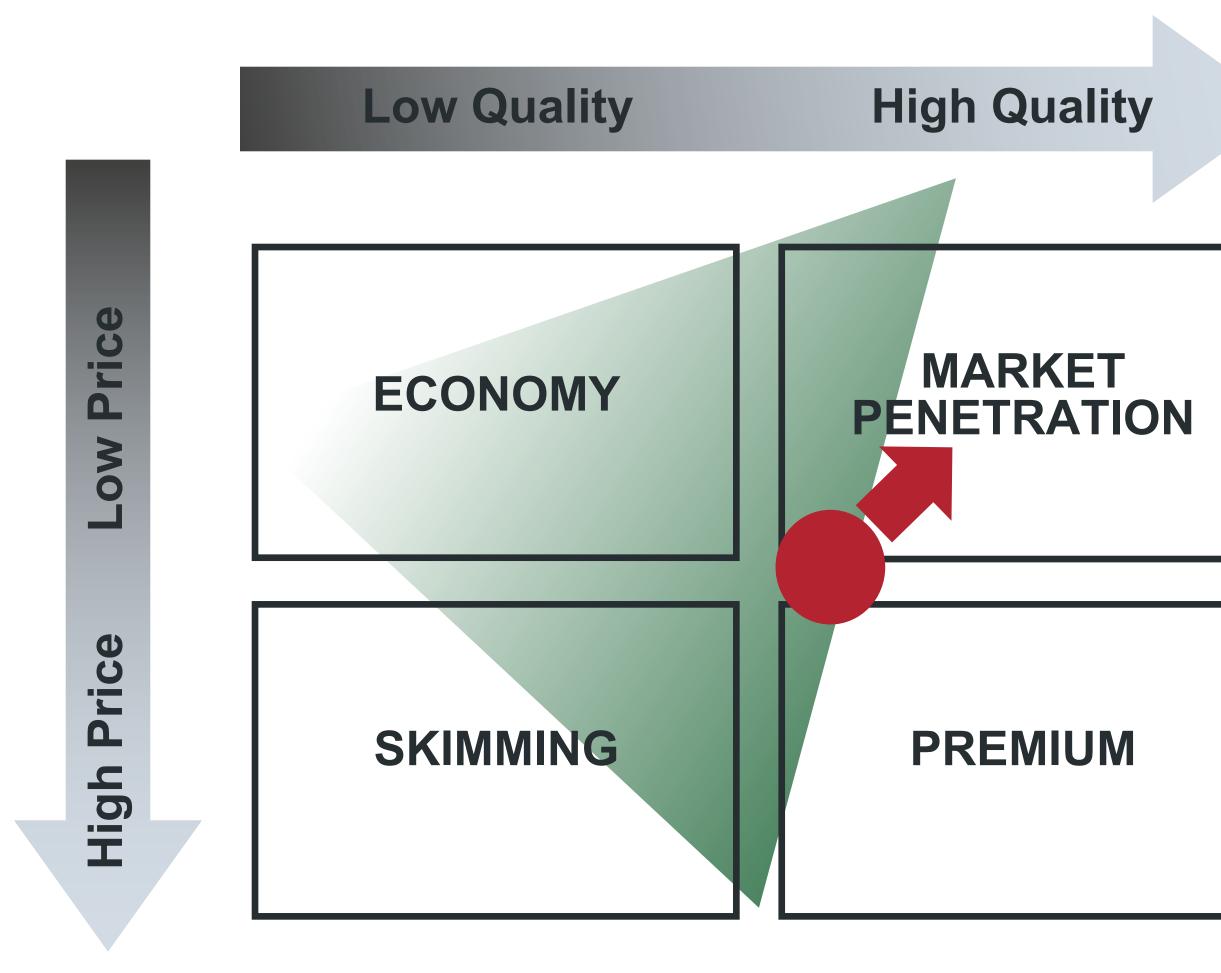


15%

Power Tool Industrial server Robot Solar Application



Pricing Strategy



Quality Is Everything

- In the power semiconductor field, the quality is more important than the technology, innovation and price.
- Through our strong supply chain, we reach the
- cost down and execute cost down by technology
 - enhancing, as chip shrinkage, higher power density.
 - We don't sacrifice the material, quality to reach the low pricing marketing.





New Product Roadmap							
	2021	2022	2023	2024			
Diode/ Rectifier	STD/ FRED SiC SBD 4A-20A, 650V/ 1200V	20A-50A	ow VF SiC SBD A, 650V/ 1200V PBR_Wave Schottky	Ultra Low VF SiC SBD 1700V Series			
MOSFET	Low/ Mid Trench GaN Cascode HEM	T, 650V	Shield Gate MOSFET 30V, 80V, 100V iC MOSFET 1200V Series	WavyFET, 40V Ultra Low RDS(on)			
IGBT		1	0A-50V, 650V FS-IGBT 150A, 1200V FS-IGBT	10V-100V IGBT By 8" Wafer Process 400V light IGBT			
Power Module				IGBT Module IGBT+ SiC SBD Module IPM Package			

Production

Develop

Plan



SiC Market Approaching Time Frame						
	2021	2022	2023	2024		
3C/ Quick Charger 電腦快充	6A-10A 650V SiC Diode DFN8X8/ TO-252	SiC	Diode with Trench/ Thin	wafer		
Motor/ industry 馬達/ 工業	6A-10A SiC Diode TO-252 For DC/DC converter					
EV 電動車		1200V SiC MOSFE 1200C SiC 650	Diode 20A			
Automobile 車用			A-10A SiC Diode TO-252 r Automotive DBC			

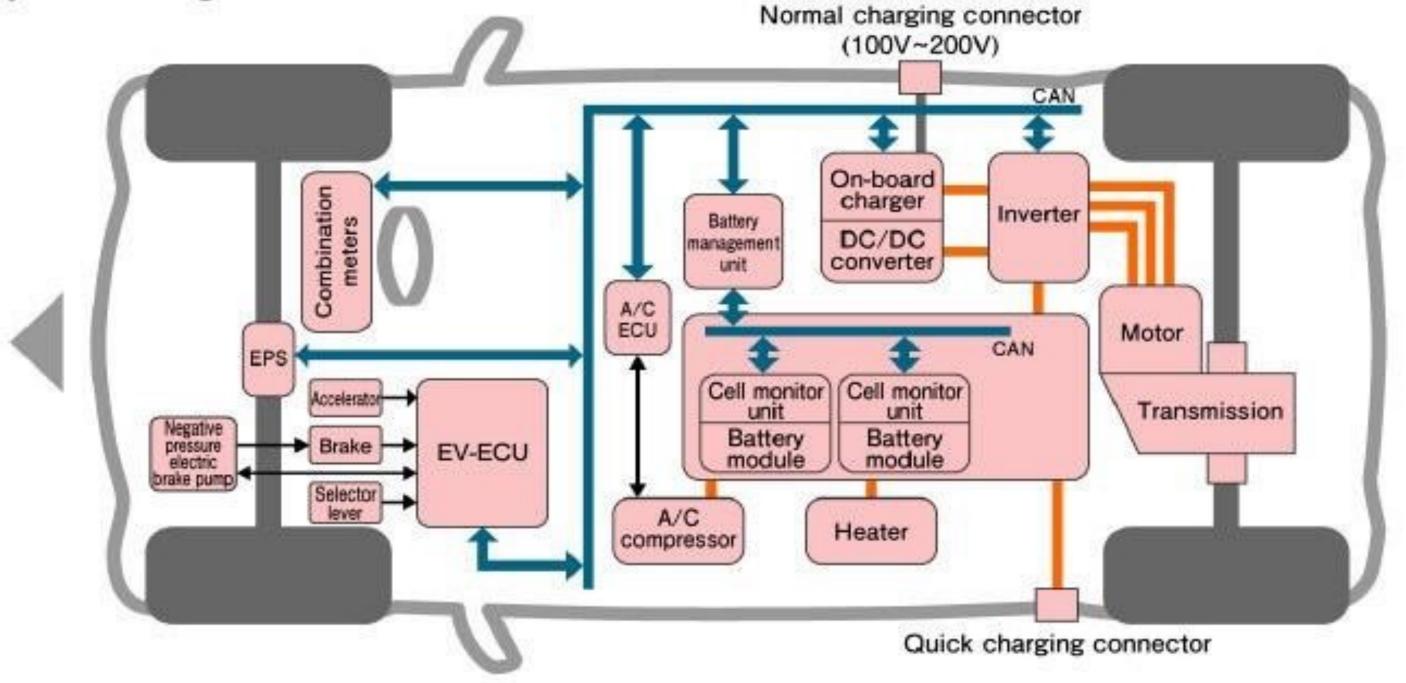
Production

Develop

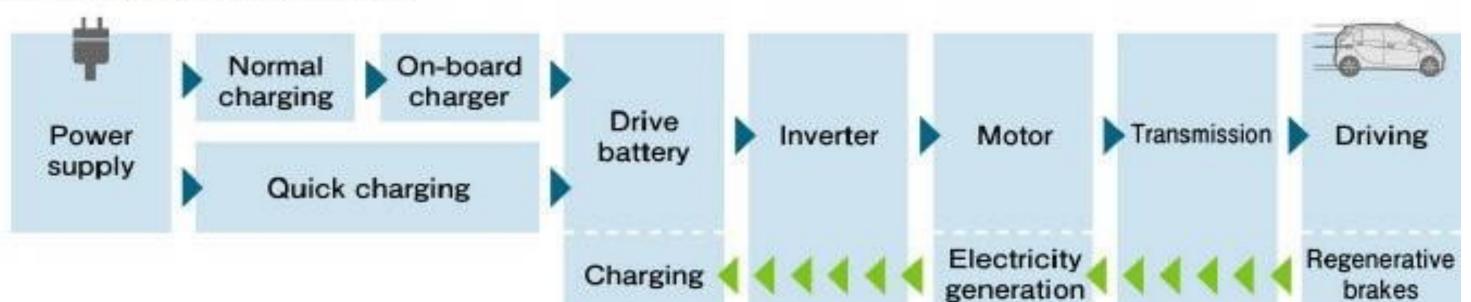
Plan

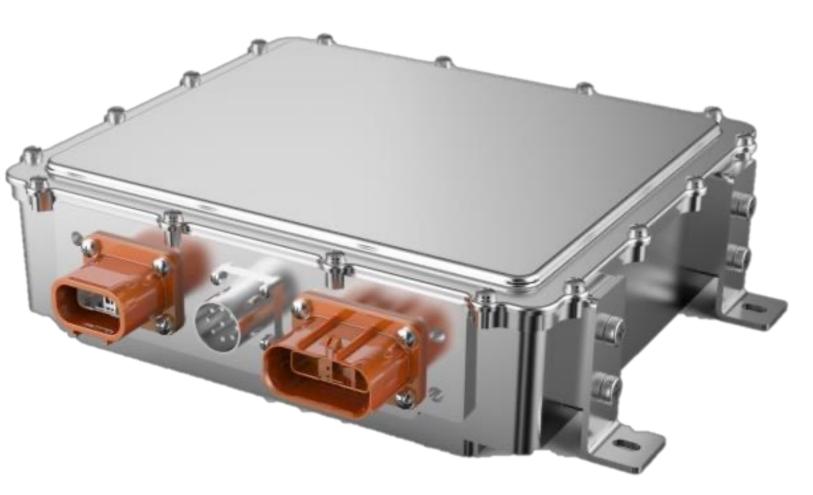
Automotive: SiC Device Application for OBC OBC (On-Board Charger) Normal charging connector

EV system configuration



Charging-to-driving process





Work with Volvo for OBC 10A, 650V with TO-252

Request SiC Device Spec:

- SIC MOSFET:
 - 1200 V, 80 m-ohm, 30 A
- SiC Schottky Diode \bullet 8A, 10A, 30A, 650V VF< 1.7V, IR< 40uA



Industry: GaN FET + SiC Technology for 300Watt Series



Electrical

Topology	LLC			
Dielectric Withstand	4000VAC Primary - Secondary			
Touch Current	< 100µA			
	EN55032 / EN55011			
EMC Standards	EN61000-3-2,3			
	EN55024 / EN61000-4-2,3,4,5,6,8,11			
MTBF	300,000 Calculated Hours at 25°C,			
	by Telcordia SR-332			



Current Si Solution:

- · Input frequency: 47-63 Hz
- · Low Profile
- · With PFC Circuit
- Efficiency: >88%

Proposal to Customer: Frequency: 250kHz Using GaN MEMT for LLC SiC Diode For PFC Circuit Efficiency up to 95%

PC Power: SiC on 電源供應器應用

Action: PFC功率因子採用SiC Diode, 驗證波形, 效率 Schedule: W1-Nov, Submit report and re-visit customer

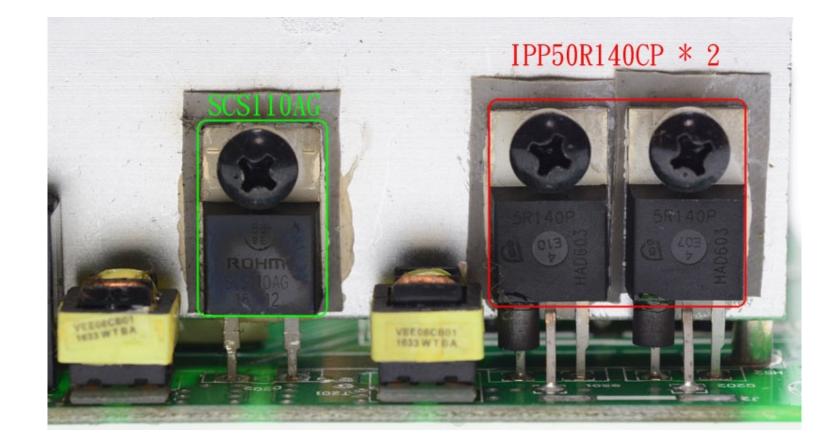
80Plus 測試種類	115V			230V				
輸出負載	10%	20%	50%	100%	10%	20%	50%	100%
80Plus	無	80%	80%	80%	無	無	無	無
80Plus 銅牌	無	82%	85%	82%	無	81%	85%	81%
80Plus 銀牌	無	85%	88%	85%	無	85%	89%	85%
80Plus 金牌	無	87%	90%	87%	無	88%	92%	88%
80Plus 白金	無	90%	92%	89%	無	90%	94%	91%
80Plus 鈦金	90%	92%	94%	90%	90%	94%	96%	91%

SEASONIC PRIME ULTRA TITANIUM

固定在散熱片上的APFC功率元件,右側紅框處為兩顆Power MOSFET, 中央綠框處為

SiC Schottky Barrier Diode (10A, 600V, TO-220AC)

2004 80Plus, 2006 能源之星列入 2016 鈦金上路, 目前通過僅27款







New Customers Application-2022





多功能变频器 Use SiC Devices

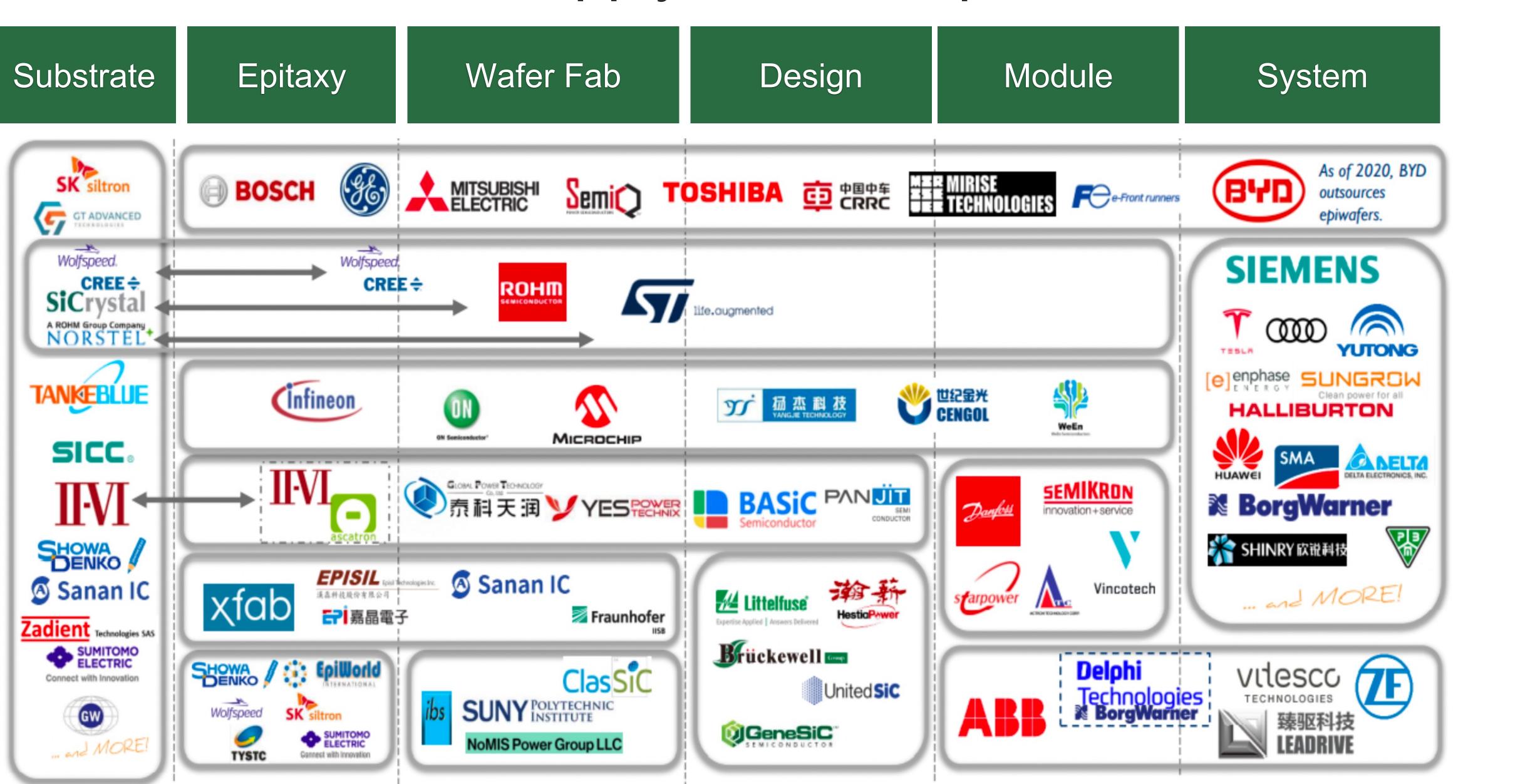


SHARP HT-SB115 Bluetooth SOUND BAR



1000W储能充电板 SiC MOSFET/ Diode

GlobalSiC Device Supply Chain Map, we are in that









Next-Generation Power Semiconductors Global key Supplier

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